CMSA75N04

N-Channel Enhancement Mode Field Effect Transistor

General Description

The CMSA75N04 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON) .
This device is ideal for load switch and battery protection applications.

Product Summary

BVDSS	RDSON	ID
40V	8mΩ	75A

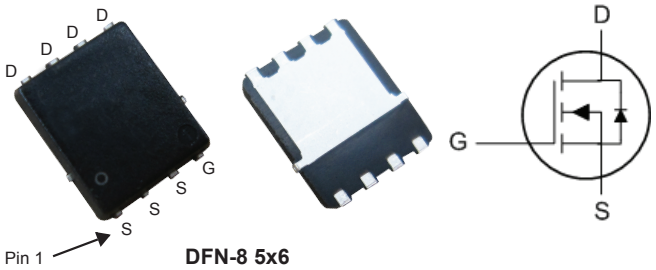
Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)

Features

- Fast switching
- Lower On-resistance
- 100% avalanche tested
- RoHS Compliant

DFN-8 5x6 Pin Configuration



DFN-8 5x6

Type	Package	Marking
CMSA75N04	DFN- 8 5*6	CMSA75N04

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current	75	A
I_D@T_C=100℃		53	A
I_{DM}	Pulsed Drain Current	225	A
EAS	Single Pulse Avalanche Energy [1]	352	mJ
P_D@T_C=25℃	Total Power Dissipation	60	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	---	50	℃/W
$R_{\theta JC}$	Thermal Resistance Junction -Case	---	2.1	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250μA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=10A	---	---	8	mΩ
		V_{GS}=4.5V, I_D=15A	---	---	11	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250μA	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=38V , V_{GS}=0V	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	28	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	7	---	Ω
Q_g	Total Gate Charge	V_{DS}=20V , I_D=20A V_{GS}=4.5V	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V , V_{GS}=10V , R_G=3.3Ω I_D =1A	---	10	---	ns
T_r	Rise Time		---	7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	26	---	
T_f	Fall Time		---	30	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	2000	---	pF
C_{oss}	Output Capacitance		---	340	---	
C_{rss}	Reverse Transfer Capacitance		---	180	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	V_G=V_D=0V , Force Current	---	---	75	A
$I_{S,pulse}$	Diode pulse current		---	---	225	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_j=25℃	---	---	1.2	V

Notes

1. The test condition is V_{DS}=25V , V_{GS}=10V , L=0.5mH , I_D=38A.